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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	HCS12
Core Size	16-Bit
Speed	25MHz
Connectivity	I²C, SCI, SPI
Peripherals	PWM, WDT
Number of I/O	59
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2.35V ~ 5.25V
Data Converters	A/D 8x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-QFP
Supplier Device Package	80-QFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc9s12a32cfuer

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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**Table 0-2 Document References** 

User Guide	Versi on	Document Order Number
HCS12 CPU Reference Manual	V02	S12CPUV2/D
HCS12 Module Mapping Control (MMC) Block Guide	V04	S12MMCV4/D
HCS12 Multiplexed External Bus Interface (MEBI) Block Guide	V03	S12MEBIV3/D
HCS12 Interrupt (INT) Block Guide	V01	S12INTV1/D
HCS12 Background Debug (BDM) Block Guide	V04	S12BDMV4/D
HCS12 Breakpoint (BKP) Block Guide	V01	S12BKPV1/D
Clock and Reset Generator (CRG) Block User Guide	V04	S12CRGV4/D
Oscillator (OSC) Block User Guide	V02	S12OSCV2/D
Enhanced Capture Timer 16 Bit 8 Channel (ECT_16B8C) Block User Guide	V01	S12ECT16B8CV1/D
Analog to Digital Converter 10 Bit 8 Channel (ATD_10B8C) Block User Guide	V02	S12ATD10B8CV2/D
Inter IC Bus (IIC) Block User Guide	V02	S12IICV2/D
Asynchronous Serial Interface (SCI) Block User Guide	V02	S12SCIV2/D
Serial Peripheral Interface (SPI) Block User Guide	V02	S12SPIV2/D
Pulse Width Modulator 8 Bit 8 Channel (PWM_8B8C) Block User Guide	V01	S12PWM8B8CV1/D
64K Byte Flash (FTS64K) Block User Guide	V01	S12FTS64KV1/D
1K Byte EEPROM (EETS1K) Block User Guide	V01	S12EETS1KV1/D
Byte Level Data Link Controller -J1850 (BDLC) Block User Guide	V01	S12BDLCV1/D
Freescale Scalable CAN (MSCAN) Block User Guide	V02	S12MSCANV2/D
Voltage Regulator (VREG) Block User Guide	V01	S12VREGV1/D
Port Integration Module (PIM_9DJ64) Block User Guide	V01	S12PIM9DJ64V1/D

- I/O lines with 5V input and drive capability
- 5V A/D converter inputs
- Operation at 50MHz equivalent to 25MHz Bus Speed
- Development support
- Single-wire background debug<sup>TM</sup> mode (BDM)
- On-chip hardware breakpoints

## 1.3 Modes of Operation

#### User modes

- Normal and Emulation Operating Modes
  - Normal Single-Chip Mode
  - Normal Expanded Wide Mode
  - Normal Expanded Narrow Mode
  - Emulation Expanded Wide Mode
  - Emulation Expanded Narrow Mode
- Special Operating Modes
  - Special Single-Chip Mode with active Background Debug Mode
  - Special Test Mode (Freescale use only)
  - Special Peripheral Mode (Freescale use only)

#### Low power modes

- Stop Mode
- Pseudo Stop Mode
- · Wait Mode

Table 1-2 Device Memory Map for MC9S12D32

Address	Module				
\$0000 - \$000F	HCS12 Multiplexed External Bus Interface	16			
\$0010 - \$0014	HCS12 Module Mapping Control	5			
\$0015 - \$0016	HCS12 Interrupt	2			
\$0017 - \$0019	Reserved	3			
\$001A - \$001B	Device ID register (PARTID)	2			
\$001C - \$001D	HCS12 Module Mapping Control	2			
\$001E	HCS12 Multiplexed External Bus Interface	1			
\$001F	HCS12 Interrupt	1			
\$0020 - \$0027	Reserved	8			
\$0028 - \$002F	HCS12 Breakpoint Module	8			
\$0030 - \$0031	HCS12 Module Mapping Control	2			
\$0032 - \$0033	HCS12 Multiplexed External Bus Interface	2			
\$0034 - \$003F	Clock and Reset Generator (PLL, RTI, COP)	12			
\$0040 - \$007F	Enhanced Capture Timer 16-bit 8 channels	64			
\$0080 - \$009F	Analog to Digital Converter 10-bit 8 channels (ATD0)	32			
\$00A0 - \$00C7	Pulse Width Modulator 8-bit 8 channels (PWM)	40			
\$00C8 - \$00CF	Serial Communications Interface 0 (SCI0)	8			
\$00D0 - \$00D7	Serial Communications Interface 0 (SCI1)	8			
\$00D8 - \$00DF	Serial Peripheral Interface (SPI0)	8			
\$00E0 - \$00E7	Inter IC Bus	8			
\$00E8 - \$00EF	Byte Data Link Controller (BDLC)	8			
\$00F0 - \$00FF	Reserved				
\$0100- \$010F	Flash Control Register	16			
\$0110 - \$011B	EEPROM Control Register	12			
\$011C - \$011F	Reserved	4			
\$0120 - \$013F	Analog to Digital Converter 10-bit 8 channels (ATD1)	32			
\$0140 - \$017F	Freescale Scalable Can (CAN0)				
\$0180 - \$023F	Reserved	192			
\$0240 - \$027F	Port Integration Module (PIM)	64			
\$0280 - \$03FF	Reserved	384			
\$0000 - \$07FF	EEPROM array 1k Array mapped twice in the address space	2048			
\$0000 - \$0FFF	RAM array, lower half (\$0000-\$07FF not usable)	4096			
\$4000 - \$7FFF	16k Fixed Flash FEPROM array (same as array from				
\$8000 - \$FFFF	\$8000 - \$FFFF 32K Fixed Flash EEPROM array				

64

#### \$001F - \$001F

### INT map 2 of 2 (HCS12 Interrupt)

Address Name \$001F **HPRIO** 

	Bit /	Bit
Read:	PSEL7	PSF
Vrite∙ l	. 0	

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
PSEL7	DSELE	DSELE	DGEI 1	DCEI 2	DGEI 3	DQEI 1	0
FSELI	FSELO	FSELS	FSEL4	FSELS	FSELZ	FSELI	

#### \$0020 - \$0027

#### Reserved

Address	Name
\$0020 -	Pagarya
\$0027	Reserve

Read:
Write:

	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
ead:	0	0	0	0	0	0	0	0
rite:								

#### \$0028 - \$002F

#### **BKP (HCS12 Breakpoint)**

Address	Name
\$0028	BKPCT0
\$0029	BKPCT1
\$002A	BKP0X
\$002B	BKP0H
\$002C	BKP0L
\$002D	BKP1X
\$002E	BKP1H
\$002F	BKP1L

	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	
Read:	ead:		DICEDIA DICE	DIZTAC	0	0	0	0	
Write:	BKEN	BKFULL	BKBDM	BKTAG					
Read:	DICOMBIL	DICOMPI	DICAMBLI	DIZAMBI	DIKODIAKE	DICODIAL	DICADIAGE	DICA DIA	
Write:	BK0MBH	BK0MBL	BK1MBH	BK1MBL	BK0RWE	BK0RW	BK1RWE	BK1RW	
Read:	0	0	DI/OV/E	DI(O)(4	DI(0)(0	DI(0)(0	DI(0)/4	DI(0)(0	
Write:			BK0V5	BK0V4	BK0V3	BK0V2	BK0V1	BK0V0	
Read:	D:445	4.4	40	40	44	40	_	D:+ 0	
Write:	Bit 15 14		13	12	11	10	9	Bit 8	
Read:	D:: 7	•	_	4		_	4	D:: 0	
Write:	Bit 7	6	5	4	3	2	1	Bit 0	
Read:	0	0	DICANG	DICANA	DICANO	DICANO.	DICALVA	DICAL/O	
Write:			BK1V5	BK1V4	BK1V3	BK1V2	BK1V1	BK1V0	
Read:	D:445	4.4	40	40	44	40	_	D:+ 0	
Write:	Bit 15   14		13	12	11	10	9	Bit 8	
Read:	D:4 7	0	-	4	0	0	4	D:4 0	
Write:	Bit 7	6	5	4	3	2	1	Bit 0	

## \$0030 - \$0031

### MMC map 4 of 4 (HCS12 Module Mapping Control)

Address	Name
\$0030	PPAGE
\$0031	Reserved

	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
Read:	0	0	PIX5	PIX4	PIX3	PIX2	PIX1	PIX0
Write:			LIVO	FIA4	FIAS	FIAZ	FIXI	FIXU
Read:	0	0	0	0	0	0	0	0
Write:								

### \$0032 - \$0033

## MEBI map 3 of 3 (HCS12 Multiplexed External Bus Interface)

Address	Name
\$0032	PORTK
\$0033	DDRK

	DIL
Read:	Bit
Write:	DIL
Read:	Bit
Write:	DIL

	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
ad: ite:	Bit 7	6	5	4	3	2	1	Bit 0
ad: ite:	Bit 7	6	5	4	3	2	1	Bit 0

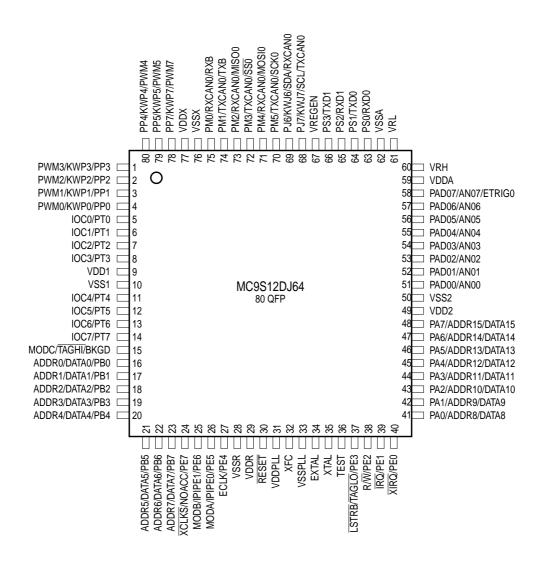


Figure 2-2 Pin Assignments in 80-pin QFP for MC9S12DJ64 and MC9S12D32

## 2.2 Signal Properties Summary

**Table 2-1** summarizes the pin functionality. Signals shown in **bold** are not available in the 80 pin package.

#### 2.3.14 PE6 / MODB / IPIPE1 — Port E I/O Pin 6

PE6 is a general purpose input or output pin. It is used as a MCU operating mode select pin during reset. The state of this pin is latched to the MODB bit at the rising edge of  $\overline{RESET}$ . This pin is shared with the instruction queue tracking signal IPIPE1. This pin is an input with a pull-down device which is only active when  $\overline{RESET}$  is low.

#### 2.3.15 PE5 / MODA / IPIPE0 — Port E I/O Pin 5

PE5 is a general purpose input or output pin. It is used as a MCU operating mode select pin during reset. The state of this pin is latched to the MODA bit at the rising edge of RESET. This pin is shared with the instruction queue tracking signal IPIPE0. This pin is an input with a pull-down device which is only active when RESET is low.

#### 2.3.16 PE4 / ECLK — Port E I/O Pin 4

PE4 is a general purpose input or output pin. It can be configured to drive the internal bus clock ECLK. ECLK can be used as a timing reference.

#### 2.3.17 PE3 / LSTRB / TAGLO — Port E I/O Pin 3

PE3 is a general purpose input or output pin. In MCU expanded modes of operation,  $\overline{LSTRB}$  can be used for the low-byte strobe function to indicate the type of bus access and when instruction tagging is on,  $\overline{TAGLO}$  is used to tag the low half of the instruction word being read into the instruction queue.

### 2.3.18 PE2 / R/W — Port E I/O Pin 2

PE2 is a general purpose input or output pin. In MCU expanded modes of operations, this pin drives the read/write output signal for the external bus. It indicates the direction of data on the external bus.

## 2.3.19 PE1 / IRQ — Port E Input Pin 1

PE1 is a general purpose input pin and the maskable interrupt request input that provides a means of applying asynchronous interrupt requests. This will wake up the MCU from STOP or WAIT mode.

## 2.3.20 PE0 / XIRQ — Port E Input Pin 0

PE0 is a general purpose input pin and the non-maskable interrupt request input that provides a means of applying asynchronous interrupt requests. This will wake up the MCU from STOP or WAIT mode.

#### 2.3.21 PH7 / KWH7 — Port H I/O Pin 7

PH7 is a general purpose input or output pin. It can be configured to generate an interrupt causing the MCU to exit STOP or WAIT mode.

#### 2.3.55 PS2 / RXD1 — Port S I/O Pin 2

PS2 is a general purpose input or output pin. It can be configured as the receive pin RXD of Serial Communication Interface 1 (SCI1).

#### 2.3.56 PS1 / TXD0 — Port S I/O Pin 1

PS1 is a general purpose input or output pin. It can be configured as the transmit pin TXD of Serial Communication Interface 0 (SCI0).

#### 2.3.57 PS0 / RXD0 — Port S I/O Pin 0

PS0 is a general purpose input or output pin. It can be configured as the receive pin RXD of Serial Communication Interface 0 (SCI0).

## 2.3.58 PT[7:0] / IOC[7:0] — Port T I/O Pins [7:0]

PT7-PT0 are general purpose input or output pins. They can be configured as input capture or output compare pins IOC7-IOC0 of the Enhanced Capture Timer (ECT).

## 2.4 Power Supply Pins

MC9S12DJ64 power and ground pins are described below.

**NOTE:** All VSS pins must be connected together in the application.

Table 2-2 MC9S12DJ64 Power and Ground Connection Summary

Mnemonic	Pin Number	Nominal	Description				
Willelilollic	112-pin QFP Vol		Description				
VDD1, 2	13, 65	2.5V	Internal power and ground generated by internal regulator				
VSS1, 2	14, 66	0V	internal power and ground generated by internal regulator				
VDDR	41	5.0V	External power and ground, supply to pin drivers and internal				
VSSR	40	0V	voltage regulator.				
VDDX	107	5.0V	External power and ground, supply to pin drivers.				
VSSX	106	0V	External power and ground, supply to pin drivers.				
VDDA	83	5.0V	Operating voltage and ground for the analog-to-digital				
VSSA	86	0V	converters and the reference for the internal voltage regulator, allows the supply voltage to the A/D to be bypassed independently.				
VRL	85	0V	Reference voltages for the analog-to-digital converter.				
VRH	84	5.0V	Therefore voltages for the analog-to-digital converter.				

**NOTE:** 

For devices assembled in 80-pin QFP packages all non-bonded out pins should be configured as outputs after reset in order to avoid current drawn from floating inputs. Refer to **Table 2-1** for affected pins.

## **5.3.2 Memory**

Refer to **Table 1-1** for locations of the memories depending on the operating mode after reset.

The RAM array is not automatically initialized out of reset.

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VDDA, VDDX, VDDR as well as VSSA, VSSX, VSSR are connected by anti-parallel diodes for ESD protection.

NOTE:

In the following context VDD5 is used for either VDDA, VDDR and VDDX; VSS5 is used for either VSSA, VSSR and VSSX unless otherwise noted.

IDD5 denotes the sum of the currents flowing into the VDDA, VDDX and VDDR

pins.

VDD is used for VDD1, VDD2 and VDDPLL, VSS is used for VSS1, VSS2 and

VSSPLL.

IDD is used for the sum of the currents flowing into VDD1 and VDD2.

#### A.1.3 Pins

There are four groups of functional pins.

#### A.1.3.1 5V I/O pins

Those I/O pins have a nominal level of 5V. This class of pins is comprised of all port I/O pins, the analog inputs, BKGD and the RESET pins. The internal structure of all those pins is identical, however some of the functionality may be disabled. E.g. for the analog inputs the output drivers, pull-up and pull-down resistors are disabled permanently.

#### A.1.3.2 Analog Reference

This group is made up by the VRH and VRL pins.

#### A.1.3.3 Oscillator

The pins XFC, EXTAL, XTAL dedicated to the oscillator have a nominal 2.5V level. They are supplied by VDDPLL.

#### **A.1.3.4 TEST**

This pin is used for production testing only.

#### **A.1.3.5 VREGEN**

This pin is used to enable the on chip voltage regulator.

## A.1.4 Current Injection

Power supply must maintain regulation within operating  $V_{DD5}$  or  $V_{DD}$  range during instantaneous and operating maximum current conditions. If positive injection current ( $V_{in} > V_{DD5}$ ) is greater than  $I_{DD5}$ , the injection current may flow out of VDD5 and could result in external power supply going out of regulation. Ensure external VDD5 load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power; e.g. if no system clock is present, or if clock rate is very low which would reduce overall power consumption.

(M) MOTOROLA

specifies results in an error of less than 1/2 LSB (2.5mV) at the maximum leakage current. If device or operating conditions are less than worst case or leakage-induced error is acceptable, larger values of source resistance is allowed.

#### A.2.2.2 Source Capacitance

When sampling an additional internal capacitor is switched to the input. This can cause a voltage drop due to charge sharing with the external and the pin capacitance. For a maximum sampling error of the input voltage  $\leq$  1LSB, then the external filter capacitor,  $C_f \geq 1024 * (C_{INS} - C_{INN})$ .

#### A.2.2.3 Current Injection

There are two cases to consider.

- 1. A current is injected into the channel being converted. The channel being stressed has conversion values of \$3FF (\$FF in 8-bit mode) for analog inputs greater than  $V_{RH}$  and \$000 for values less than  $V_{RL}$  unless the current is higher than specified as disruptive condition.
- 2. Current is injected into pins in the neighborhood of the channel being converted. A portion of this current is picked up by the channel (coupling ratio K), This additional current impacts the accuracy of the conversion depending on the source resistance.
  - The additional input voltage error on the converted channel can be calculated as  $V_{ERR} = K * R_S * I_{INJ}$ , with  $I_{INJ}$  being the sum of the currents injected into the two pins adjacent to the converted channel.

Table A-9 ATD Electrical Characteristics

Condit	ions	s are shown in Table A-4 unless otherwise noted					
Num	С	Rating	Symbol	Min	Тур	Max	Unit
1	С	Max input Source Resistance	R <sub>S</sub>	-	-	1	ΚΩ
2	Т	Total Input Capacitance Non Sampling Sampling	C <sub>INN</sub> C <sub>INS</sub>			10 22	pF
3	С	Disruptive Analog Input Current	I <sub>NA</sub>	-2.5		2.5	mA
4	С	Coupling Ratio positive current injection	K <sub>p</sub>			10 <sup>-4</sup>	A/A
5	С	Coupling Ratio negative current injection	K <sub>n</sub>			10 <sup>-2</sup>	A/A

## A.3 NVM, Flash and EEPROM

**NOTE:** Unless otherwise noted the abbreviation NVM (Non Volatile Memory) is used for both Flash and EEPROM.

### A.3.1 NVM timing

The time base for all NVM program or erase operations is derived from the oscillator. A minimum oscillator frequency f<sub>NVMOSC</sub> is required for performing program or erase operations. The NVM modules do not have any means to monitor the frequency and will not prevent program or erase operation at frequencies above or below the specified minimum. Attempting to program or erase the NVM modules at a lower frequency a full program or erase transition is not assured.

The Flash and EEPROM program and erase operations are timed using a clock derived from the oscillator using the FCLKDIV and ECLKDIV registers respectively. The frequency of this clock must be set within the limits specified as f<sub>NVMOP</sub>.

The minimum program and erase times shown in **Table A-11** are calculated for maximum  $f_{NVMOP}$  and maximum  $f_{bus}$ . The maximum times are calculated for minimum  $f_{NVMOP}$  and a  $f_{bus}$  of 2MHz.

#### A.3.1.1 Single Word Programming

The programming time for single word programming is dependant on the bus frequency as a well as on the frequency  $f_{NVMOP}$  and can be calculated according to the following formula.

$$t_{swpgm} = 9 \cdot \frac{1}{f_{NVMOP}} + 25 \cdot \frac{1}{f_{bus}}$$

## A.3.1.2 Row Programming

This applies only to the Flash where up to 32 words in a row can be programmed consecutively by keeping the command pipeline filled. The time to program a consecutive word can be calculated as:

$$t_{\text{bwpgm}} = 4 \cdot \frac{1}{f_{\text{NVMOP}}} + 9 \cdot \frac{1}{f_{\text{bus}}}$$

The time to program a whole row is:

$$t_{brpqm} = t_{swpqm} + 31 \cdot t_{bwpqm}$$

Row programming is more than 2 times faster than single word programming.

#### A.3.1.3 Sector Erase

Erasing a 512 byte Flash sector or a 4 byte EEPROM sector takes:

## A.3.2 NVM Reliability

The reliability of the NVM blocks is guaranteed by stress test during qualification, constant process monitors and burn-in to screen early life failures.

The failure rates for data retention and program/erase cycling are specified at the operating conditions noted.

The program/erase cycle count on the sector is incremented every time a sector or mass erase event is executed.

Table A-12 NVM Reliability Characteristics

Condit	Conditions are shown in Table A-4 unless otherwise noted								
Num	С	Rating	Symbol	Min	Тур	Max	Unit		
1	С	Data Retention at an average junction temperature of $T_{Javg} = 85^{\circ}C^{1}$	t <sub>NVMRET</sub>	15			Years		
2	С	Flash number of Program/Erase cycles	n <sub>FLPE</sub>	10,000			Cycles		
3	С	EEPROM number of Program/Erase cycles (–40°C $\leq$ T <sub>J</sub> $\leq$ 0°C)	n <sub>EEPE</sub>	10,000			Cycles		
4	С	EEPROM number of Program/Erase cycles $(0^{\circ}\text{C} < \text{T}_{\text{J}} \le 140^{\circ}\text{C})$	n <sub>EEPE</sub>	100,000			Cycles		

#### NOTES:

<sup>1.</sup> Total time at the maximum guaranteed device operating temperature <= 1 year

# A.8 External Bus Timing

A timing diagram of the external multiplexed-bus is illustrated in **Figure A-9** with the actual timing values shown on table **Table A-20**. All major bus signals are included in the diagram. While both a data write and data read cycle are shown, only one or the other would occur on a particular bus cycle.

### A.8.1 General Muxed Bus Timing

The expanded bus timings are highly dependent on the load conditions. The timing parameters shown assume a balanced load across all outputs.

## B.2 112-pin LQFP package

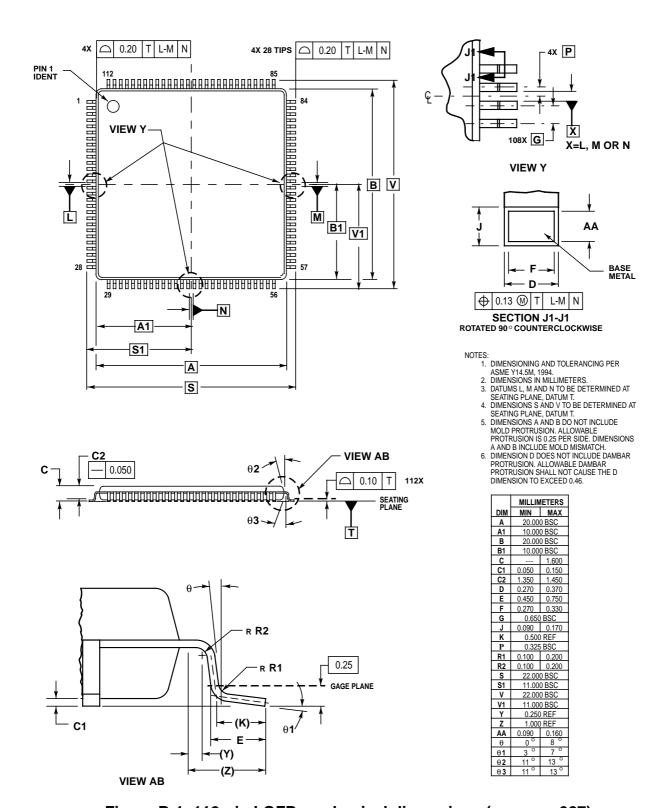


Figure B-1 112-pin LQFP mechanical dimensions (case no. 987)